



U.S. Patent Docket No.: JCLA7289

Serial No.: 09/990,397

Handwritten: #4/1/02, W/extra, 9-20-02, 10/5/02

IN THE UNITED STATES PATENT AND TRADEMARK OFFICE

re PATENT APPLICATION of

Applicants : Jung-Yu Hsieh)

Serial No. : 09/990,397)

Examiner: Lewis, Monica

Filed : November 20, 2001)

Group Art Unit: 2822

For : Flash Memory Structure)

AMENDMENT AND RESPONSE TO OFFICE ACTION

Assistant Commissioner for Patents
Washington, D.C. 20231

Dear Sir:

The Office Action mailed April 22, 2002 (Paper No. 2), has been carefully considered. In response thereto, please enter the following amendments and consider the following remarks.

Amendment

FOR THE SPECIFICATION:

Please substitute the specification with the following paragraphs with the same numberings.

[0024] Moreover, whether or not to leave out the second oxide layer 216 between the high dielectric constant dielectric layer 214 and the control gate 208 within the dielectric stacked layer 210 is decided according to the band gap size of the high dielectric constant dielectric layer 214 used. If the band gap of the utilized high dielectric constant dielectric layer 214 is as wide or is

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